Nuclear Instruments and Methods in Physics Research 21 (1987) 639–648
North-Holland, Amsterdam

AUTHOR INDEX

Abel, F., B. Agius and J. Gyulai, Absolute determination of 10^{12} cm^{-2} As in Si by RBS microanalysis (*Letter to the Editor*) B21 (1987) 77
Adishchev, Yu.N., A.N. Didenko, V.V. Mun, G.A. Pleshkov, A.P. Potylitsin, V.K. Tomchakov, S.R. Uglov and S.A. Vorobiev, Measurements of parametric X-rays from relativistic electrons in silicon crystals B21 (1987) 49
Aebi, V.W., see Ho, P. B21 (1987) 581
Agius, B., see Abel, F. B21 (1987) 77
Aitken, D., The precision implant 9000 beam line B21 (1987) 274
Aitken, D., see Steen, L.S. B21 (1987) 328
Aitken, D., S. Mehta, N. Parisi, C.J. Russo and V. Schwartz, A new VLSI compatible rapid thermal processing system B21 (1987) 627
Angelo, G., see Jost, J. B21 (1987) 372
Augulis, L., see Domkus, M. B21 (1987) 480
Augulis, L., B. Jasiulionis and L. Pranevičius, Development of surface topology during ion sputtering of silicon B21 (1987) 608

Baerg, W., see Tzeng, J.C. B21 (1987) 112
Baker, J.A., see Ingram, D.C. B21 (1987) 460
Baker, J.A., see Rai, A.K. B21 (1987) 466
Bannenberg, J.G., see Koudijs, R. B21 (1987) 296
Barth, M., see Wolf, G.K. B21 (1987) 570
Basra, V.K., C.M. McKenna and S.B. Felch, A study of wafer and device charging during high current ion implantation B21 (1987) 360
Basra, V.K., see Liebert, R.B. B21 (1987) 391
Basra, V.K. and D.F. Downey, RTP shallow junction formation of low energy boron implants into pre-amorphized silicon B21 (1987) 505
Benveniste, V., Wafer cooling in a high current ion implanter B21 (1987) 366
Bernhardt, D., see Glavish, H.F. B21 (1987) 264
Biasse, B., A.M. Cartier, P. Spinelli and M. Bruel, Formation of shallow P^+N junctions by dual F^+/B^+ implantation B21 (1987) 493
Binder, H., see Kakoschke, R. B21 (1987) 142
Biondo, L., see Outcault, R. B21 (1987) 354
Biosseau, P., see Glavish, H.F. B21 (1987) 264
Bitensky, I.S. and E.S. Parilis, Shock wave mechanism for cluster emission and organic molecule desorption under heavy ion bombardment B21 (1987) 26
Blake, J., see Gelpey, J.C. B21 (1987) 612
Booker, G.R., see Hemment, P.L.F. B21 (1987) 129
Brack, K., W. Euen and D. Hagmann, Discharge of P^{2+} ions in the beamline of medium current implanters B21 (1987) 405
Bricault, R.J., P. Sioshansi and S.N. Bunker, Deposition of boron nitride thin films by ion beam assisted deposition B21 (1987) 586
Brick, R., see Lundquist, P. B21 (1987) 414
Bright, N., see Steen, L.S. B21 (1987) 328
Bright, N.J., see Southwood, P.D. B21 (1987) 514
Brown, I. and J. Washburn, The MEVVA ion source for high current metal ion implantation B21 (1987) 201
Bruel, M., see Spinelli, P. B21 (1987) 452
Bruel, M., see Biasse, B. B21 (1987) 493
Bunker, S.N., P. Sioshansi, M. Sanfacon, A. Mogro-Campero and G.A. Smith, Analysis of buried layers from high dose oxygen ion implantation B21 (1987) 148
Bunker, S.N., see Bricault, R.J. B21 (1987) 586

Cai Weiping, see Tian Wei B21 (1987) 597
Cao Niansen, see Tian Wei B21 (1987) 597
Cartier, A.M., see Spinelli, P. B21 (1987) 452
Cartier, A.M., see Biasse, B. B21 (1987) 493
Celler, G.K., see Hemment, P.L.F. B21 (1987) 129

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Chapman, G.E., D.J. O'Connor and R.J. MacDonald, The scattering of doubly charged ions from surfaces B21 (1987) 20
Chater, R.J., see Hemment, P.L.F. B21 (1987) 129
Chen, J.T.C., Monitoring low dose single implanted layers with four-point probe technology B21 (1987) 526
Chen Huanzheng, see Jin Jiucheng B21 (1987) 610
Cheung, N.W., see Deng, E. B21 (1987) 134
Cheung, N.W., see Wong, H. B21 (1987) 447
Chopra, K.L., see Shrivastava, S. B21 (1987) 591
Chu, P.K., see Wong, H. B21 (1987) 447
Chung, Y., see Ho, P. B21 (1987) 581
Corey, P., see Lundquist, P. B21 (1987) 414
Crowley, J., see Kermani, A. B21 (1987) 633
Cui, F.-Z., H.-D. Li and J.-P. Zhang, Computer simulations of the ion implantation process in layered materials B21 (1987) 478

Davis, J.R., see Hemment, P.L.F. B21 (1987) 129
Debolske, T., see Kermani, A. B21 (1987) 633
Deng, E., H. Wong and N.W. Cheung, Effects of high energy boron ions implanted in MOSFETs B21 (1987) 134
Deng, E., see Wong, H. B21 (1987) 447
Denholm, A.S., see Glavish, H.F. B21 (1987) 264
DiBitonto, D., R. Huson, P. McIntyre, A. Nassiri, D. Raparia and C. Swenson, Multi-MeV ion implantation accelerator system B21 (1987) 155
Didenko, A.N., see Adishchev, Yu.N. B21 (1987) 49
Dolan, R.P., see Douglas-Hamilton, D.H. B21 (1987) 158
Domkus, M., L. Augulis, L. Pranevičius, L. Puodžiukynas and G. Zubauskas, Study of mechanical strains in implanted silicon slices B21 (1987) 480
Douglas-Hamilton, D.H., R.P. Dolan and H.E. Friedman, Layer thicknesses in oxygen implantation of silicon . B21 (1987) 158
Douglas-Hamilton, D.H., see Ruffell, J.P. B21 (1987) 229
Douglas-Hamilton, D.H., see Kaim, R.E. B21 (1987) 321
Douglas-Hamilton, D.H., J.P. Ruffell, R.E. Kaim and K. Izumi, End station design and wafer quality control for a high current oxygen implanter B21 (1987) 324
Downey, D.F., see Liebert, R.B. B21 (1987) 391
Downey, D.F., see Basra, V.K. B21 (1987) 505
Drach, J., see Price, P.B. B21 (1987) 60
Dubbelman, P., see Koudijs, R. B21 (1987) 296

Eddy, R., A. Long, S. Smith and J. Tkach, Improvements in dose uniformity on high current ion implantation systems B21 (1987) 424
Ehlers, K.W., see Walther, S.R. B21 (1987) 215
Ensinger, W., see Wolf, G.K. B21 (1987) 570
Euen, W., see Brack, K. B21 (1987) 405
Evans, D.C., A generalized mathematical model for wafer cooling with gas B21 (1987) 385

Felch, S.B., see Basra, V.K. B21 (1987) 360
Felch, S.B. and R.A. Powell, Use of ultra-low-energy BF_2^+ implantation and rapid annealing to avoid channeling effects in shallow junction formation B21 (1987) 486
Feng Xiqi, Wei Zongying and Zou Weiyuan, Ion-beam-induced decomposition of bismuth germanium oxide crystal surfaces B21 (1987) 576
Fried, M., see Krafcsik, I. B21 (1987) 604
Friedman, H.E., see Douglas-Hamilton, D.H. B21 (1987) 158
Fujisawa, H., see Kawai, T. B21 (1987) 239
Fukui, R., see Yabe, E. B21 (1987) 190
Fukui, R., see Tonegawa, A. B21 (1987) 212
Fukui, R., see Uchiyama, T. B21 (1987) 306
Fukumaru, F., see Matsuda, K. B21 (1987) 314

Galkute, L., L. Pranevičius and G. Zubauskas, Model of preferential sputtering of multicomponent materials induced by low energy ions B21 (1987) 46
Gamo, K., see Yuba, Y. B21 (1987) 151
Garvey, E. and L. Zimmermann, Robotics and host computer interface for NV-10 high current implanters B21 (1987) 509
Gelpey, J.C., P.O. Stump, J. Blake, A. Michel and W. Rausch, Uniformity characterization of an RTP system .. B21 (1987) 612
Gerber, J., see Simonis, H.J. B21 (1987) 56
Gerbier, G., see Price, P.B. B21 (1987) 60

Ghanbari, E., Basics of ion sources in BASIC (BIOSIB) ... B21 (1987) 198
Giacomozzi, F., see Margesin, B. ... B21 (1987) 566
Gibbons, J.F., Historical perspectives on ion implantation ... B21 (1987) 83
Giles, I.S. and C.G. Wilson, A simple bevelling technique for the depth-profiling of deuterium in steels ... B21 (1987) 72
Glavish, H.F., Radio-frequency linear accelerators for ion implanters ... B21 (1987) 218
Glavish, H.F., D. Bernhardt, P. Biosseau, B. Libby, G. Simcox and A.S. Denholm, Production high energy ion implanters using radio frequency acceleration ... B21 (1987) 264
Glawischnig, H., see Hall, J.M. ... B21 (1987) 350
Glaze, J.A., see Golin, J.R. ... B21 (1987) 542
Golding, L., see Schuur, J. ... B21 (1987) 554
Golin, J.R., N.W. Schell, J.A. Glaze and R.G. Ozarski, Latest advances in ion implant optical dosimetry ... B21 (1987) 542
Gotoh, Y., see Ishikawa, J. ... B21 (1987) 186
Grant, J., see Taylor, C. ... B21 (1987) 224
Green, T.S., see Proudfoot, G. ... B21 (1987) 300
Gregory, R.B., see Wilson, S.R. ... B21 (1987) 433
Gupta, D.K., see Pal, P.B. ... B21 (1987) 14
Guzman, L., see Margesin, B. ... B21 (1987) 566
Gyulai, J., see Abel, F. ... B21 (1987) 77
Gyulai, J., see Krafcsik, I. ... B21 (1987) 604

Hagelberg, F., see Simonis, H.J. ... B21 (1987) 56
Hagmann, D., see Brack, K. ... B21 (1987) 405
Hall, J.M., see Steen, L.S. ... B21 (1987) 328
Hall, J.M., H. Glawischnig and W. Holtschmidt, Charging studies in applied metarials precision implant 9000 system ... B21 (1987) 350
Hashimoto, H., see Miyauchi, E. ... B21 (1987) 104
Hatori, T., see Takeshiro, S. ... B21 (1987) 209
Hemment, P.L.F., K.J. Reeson, J.A. Kilner, R.J. Chater, C. Marsh, G.R. Booker, J.R. Davis and G.K. Celler, Novel dielectric/silicon planar structures formed by ion beam synthesis ... B21 (1987) 129
Higashi, H., A. Soni, L. Martinez and K. Week, Process yield improvements with process control terminal for Varian serial ion implanters ... B21 (1987) 518
Hight, B.H., see King, M.L. ... B21 (1987) 396
Ho, P., Y. Chung and V.W. Aebi, Rapid thermal annealing of arsenic, beryllium and zinc dual implanted AlGaAs ... B21 (1987) 581
Hodul, D.T., see Smith, H.E. ... B21 (1987) 503
Hodul, D.T., see Mehta, S. ... B21 (1987) 629
Holden, S., see Taylor, C. ... B21 (1987) 224
Holtschmidt, W., see Hall, J.M. ... B21 (1987) 350
Hoogerbrugge, R. and P.G. Kistemaker, Analytical expressions for the internal and kinetic energy distributions of sputtered clusters and molecules ... B21 (1987) 37
Hu, C., see Zappe, H.P. ... B21 (1987) 163
Huson, R., see DiBitonto, D. ... B21 (1987) 155

Ingram, D.C., J.A. Baker, D.A. Walsh and E. Strathman, Range distributions of MeV implants in silicon II. A comparison of SIMS and spreading resistance profiles of B, P and Ga ... B21 (1987) 460
Ingram, D.C., see Rai, A.K. ... B21 (1987) 466
Inman, M., see Proudfoot, G. ... B21 (1987) 300
Inoue, M., see Yoshida, M. ... B21 (1987) 483
Inoue, N., see Katagawa, T. ... B21 (1987) 194
Ishida, T., see Yuba, Y. ... B21 (1987) 151
Ishikawa, J., Y. Gotoh, H. Tsuji and T. Takagi, Impregnated-electrode-type liquid metal ion source ... B21 (1987) 186
Ishikawa, J., K. Ogawa, K. Miyata, H. Tsuji and T. Takagi, Negative ion source (NIABNIS) and preparation of transparent carbon films by negative carbon ion beam deposition ... B21 (1987) 205
Ishizaka, N., see Yabe, E. ... B21 (1987) 190
Isoya, A., see Uchiyama, T. ... B21 (1987) 306
Iwaki, M., see Ohira, S. ... B21 (1987) 588
Izumi, K., Applications of SIMOX technology to CMOS LSI and radiation-hardened devices ... B21 (1987) 124
Izumi, K., see Ruffell, J.P. ... B21 (1987) 229
Izumi, K., see Douglas-Hamilton, D.H. ... B21 (1987) 324

Jain, A., see Shrivastava, S. ... B21 (1987) 591

Jasiulionis, B., see Augulis, L. . . . B21 (1987) 608
Jiang Xin Yuan, Lu Shi Wan and Shi Zhi Zu, A 600 keV research heavy ion implanter . . . B21 (1987) 310
Jin Jiucheng, Luo Yingming, Zhao Chuanguo and Chen Huanzheng, Some experimental studies on GCr15 steel by nitrogen ion overlap-implantation . . . B21 (1987) 610
Johnson, W.H., see Smith, A.K. . . . B21 (1987) 529
Jones, K.S., see Prussin, S. . . . B21 (1987) 496
Jones, K.S., S. Prussin and E.R. Weber, The effect of implant species on defect anneal kinetics part II: arsenic and germanium implantation . . . B21 (1987) 499
Jost, J., G. Angelo and J. Turner, 0.5 μm particulate performance of a batch process implanter . . . B21 (1987) 372
Joyce, L.F., see O'Connor, J.P. . . . B21 (1987) 334

Kaim, R.E., see Ruffell, J.P. . . . B21 (1987) 229
Kaim, R.E., D.H. Douglas-Hamilton and J.P. Ruffell, Accelaration column for a high current oxygen implanter B21 (1987) 321
Kaim, R.E., see Douglas-Hamilton, D.H. . . . B21 (1987) 324
Kakoschke, R., H. Binder, S. Röhl, K. Masseli, I.W. Rangelow, S. Saler and R. Kassing, Ion implantation into three-dimensional structures . . . B21 (1987) 142
Kalbfus, C.R. and R. Milgate, Recent improvements in double charged ion beam energy purity for serial process ion implanters . . . B21 (1987) 400
Kang, H.J., see Saito, T. . . . B21 (1987) 456
Kao, T.-M. and T.W. Sigmon, $^{11}B^{+}$ implantation and postimplant anneal studies in $Hg_{1-x}Cd_xTe$ . . . B21 (1987) 578
Kassing, R., see Kakoschke, R. . . . B21 (1987) 142
Katagawa, T., O. Tsukakoshi, S. Komiya and N. Inoue, Application of a 3-D computer simulation code for ion beam extraction with a high current Freeman type ion source . . . B21 (1987) 194
Katagawa, T., see Komatsu, K. . . . B21 (1987) 235
Katagawa, T., see Uchiyama, T. . . . B21 (1987) 306
Kawai, T., M. Naitoh, M. Nogami, T. Kinoyama, N. Nagai and H. Fujisawa, PR-80 high current ion implantation machine . . . B21 (1987) 239
Keenan, W.A., see Smith, A.K. . . . B21 (1987) 529
Keenan, W.A., Bridging implant technique to characterize MeV implants . . . B21 (1987) 563
Kennedy, G.L., see Larson, L.A. . . . B21 (1987) 421
Kermani, A., T. Debolske, J. Crowley and T. Stultz, Process control of titanium silicide formation using rapid thermal processing . . . B21 (1987) 633
Kikuchi, R., see Yabe, E. . . . B21 (1987) 190
Kikuchi, R., see Tonegawa, A. . . . B21 (1987) 212
Kikuchi, R., see Uchiyama, T. . . . B21 (1987) 306
Kilner, J.A., see Hemment, P.L.F. . . . B21 (1987) 129
King, M.L., S.E. Sampayan and B.H. Hight, A method of surface charge neutralization during ion implantation B21 (1987) 396
Kinoyama, T., see Kawai, T. . . . B21 (1987) 239
Kiralyhidi, L., see Krafcsik, I. . . . B21 (1987) 604
Kirby, B.J., L.A. Larson and R.-Y. Liang, Thermal-wave measurements of ion implanted silicon . . . B21 (1987) 550
Kistemaker, P.G., see Hoogerbrugge, R. . . . B21 (1987) 37
Kleppinger, R., see Smith, A.K. . . . B21 (1987) 529
Knopp, M., see Simonis, H.J. . . . B21 (1987) 56
Komatsu, K., K. Takagi, O. Tsukakoshi, T. Katagawa, E. Kouno and S. Komiya, High current ion implanter aimed at clean and dust-free production . . . B21 (1987) 235
Komatsu, K., K. Yui, T. Terasawa, K. Niikura, E. Kouno and S. Komiya, A high throughput end station of a high current ion implanter . . . B21 (1987) 317
Komiya, S., see Yabe, E. . . . B21 (1987) 190
Komiya, S., see Katagawa, T. . . . B21 (1987) 194
Komiya, S., see Tonegawa, A. . . . B21 (1987) 212
Komiya, S., see Komatsu, K. . . . B21 (1987) 235
Komiya, S., see Uchiyama, T. . . . B21 (1987) 306
Komiya, S., see Komatsu, K. . . . B21 (1987) 317
Komiya, S., see Saito, T. . . . B21 (1987) 456
Konishi, M., see Matsuda, K. . . . B21 (1987) 314
Koshikawa, T., see Uchiyama, T. . . . B21 (1987) 306
Koudijs, R., P. Dubbelman, W.H. Urbanus and J.G. Bannenberg, A 1 and 2 MV ion implantation facility . . . B21 (1987) 296
Kouno, E., see Komatsu, K. . . . B21 (1987) 235
Kouno, E., see Komatsu, K. . . . B21 (1987) 317
Krafcsik, I., L. Kiralyhidi, P. Riedl, M. Fried, J. Gyulai and F. Pavlyak, Repetitive mode pulsed ion implanter with magnetically insulated diode . . . B21 (1987) 604

Kuduk, R., see Mączka, D. B21 (1987) 521
Kunkel, W.B., see Walther, S.R. B21 (1987) 215

Lamartine, B.C., see Wilson, S.R. B21 (1987) 433
Larson, L.A. and G.L. Kennedy, Dosing accuracy: a comparison of several experiments B21 (1987) 421
Larson, L.A., see Kirby, B.J. B21 (1987) 550
Latuszyński, A., see Mączka, D. B21 (1987) 521
Lazzari, G., see Margesin, B. B21 (1987) 566
Leavitt, J.A., see Wilson, S.R. B21 (1987) 433
Leung, K.N., see Walther, S.R. B21 (1987) 215
Li, H.-D., see Cui, F.-Z. B21 (1987) 478
Li Jiun, see Tian Wei B21 (1987) 597
Li Junping, see Ma Mingxiu B21 (1987) 182
Liang, R.-Y., see Kirby, B.J. B21 (1987) 550
Libby, B., see Glavish, H.F. B21 (1987) 264
Liebert, R.B., D.F. Downey and V.K. Basra, Planar channeling effects in a batch process ion implanter B21 (1987) 391
Lin Cheng-lu and Tsou Shih-chang, Dopant redistribution of As-implanted SOI films during rapid thermal annealing B21 (1987) 627
Liu Xiang-huai, Tsou Shih-chang and Tu Yu-shen, Improvement of secondary electron emission characteristics by ion implantation B21 (1987) 595
Long, A., see Eddy, R. B21 (1987) 424
Lu Shi Wan, see Jiang Xin Yuan B21 (1987) 310
Lundquist, P., C. McKenna, R. Brick and P. Corey, New dosimetry system for a serial process ion implanter B21 (1987) 414
Luo Yingming, see Jin Jiucheng B21 (1987) 610

Ma Mingxiu, Li Junping and Zhou Fengsheng, A hollow cold cathode multipurpose ion source B21 (1987) 182
MacDonald, R.J., see Chapman, G.E. B21 (1987) 20
Mączka, D., A. Latuszyński, R. Kuduk and J. Partyka, Optimization of the ion implantation process B21 (1987) 521
Mahony, C.M.O., see Proudfoot, G. B21 (1987) 300
Maneval, J., see Schuur, J. B21 (1987) 554
Margesin, B., F. Giacomozzi, L. Guzman, G. Lazzari and V. Zanini, An apparatus for combined vapor deposition and ion implantation to modify the surface properties of metals B21 (1987) 566
Marinescu, R., An etch-study of ion implanted SiO_2 films B21 (1987) 428
Marsh, C., see Hemment, P.L.F. B21 (1987) 129
Martan, J., Determination of the implanted dopants distribution by Pearson's function B21 (1987) 476
Martinez, L., see Higashi, H. B21 (1987) 518
Masseli, K., see Kakoschke, R. B21 (1987) 142
Matsuda, K., F. Fukumaru, Y. Mizutani, M. Konishi and K. Matsunaga, Large diameter ion beam implantation system B21 (1987) 314
Matsunaga, K., see Matsuda, K. B21 (1987) 314
McCormick, A.W., see Rai, A.K. B21 (1987) 466
McGuire, E., 0.1% ultra-uniformity in electrostatically scanned ion implantation systems B21 (1987) 431
McIntyre Jr, L.C., see Wilson, S.R. B21 (1987) 433
McIntyre, P., see DiBitonto, D. B21 (1987) 155
McKenna, C., see Outcault, R. B21 (1987) 354
McKenna, C., see Lundquist, P. B21 (1987) 414
McKenna, C.M., see Basra, V.K. B21 (1987) 360
Mehta, S., see Aitken, D. B21 (1987) 622
Mehta, S., D.T. Hodul and C.J. Russo, Studies of thin oxides grown by rapid thermal processing B21 (1987) 629
Michel, A., see Gelpey, J.C. B21 (1987) 612
Mihara, Y., see Uchiyama, T. B21 (1987) 306
Milgate, R. and R. Simonton, Recent improvements in the particle performance of a Varian 350D ion implanter B21 (1987) 381
Milgate, R., see Kalbfus, C.R. B21 (1987) 400
Mitani, E., see Tamura, M. B21 (1987) 438
Miyata, K., see Ishikawa, J. B21 (1987) 205
Miyauchi, E. and H. Hashimoto, Maskless ion implantation system for three-dimensional fine doping structures in III–V compound semiconductors B21 (1987) 104
Mizutani, Y., see Matsuda, K. B21 (1987) 314
Modgil, S.K., see Virk, H.S. B21 (1987) 68
Moffatt, S., A 100 mA class ion implanter for large scale production of buried oxide SOI wafers B21 (1987) 251
Mogro-Campero, A., see Bunker, S.N. B21 (1987) 148

Morrison, G.H., see Smith, H.E. . . . B21 (1987) 503
Mun, V.V., see Adishchev, Yu.N. . . . B21 (1987) 49
Myron, D.D. and D.R. Zrudsky, Implant uniformity improvement using advanced scanning techniques . . . B21 (1987) 410

Naden, J.M., see Weiss, B.L. . . . B21 (1987) 584
Nagai, N., see Kawai, T. . . . B21 (1987) 239
Naitoh, M., see Kawai, T. . . . B21 (1987) 239
Namba, S., see Yuba, Y. . . . B21 (1987) 151
Nassiri, A., see DiBitonto, D. . . . B21 (1987) 155
Natsukai, N., see Tamura, M. . . . B21 (1987) 438
Niikura, K., see Komatsu, K. . . . B21 (1987) 317
Nogami, M., see Kawai, T. . . . B21 (1987) 239
Norton, G.A., see Rathmell, R.D. . . . B21 (1987) 270

O'Connor, D.J., see Chapman, G.E. . . . B21 (1987) 20
O'Connor, J.P. and L.F. Joyce, A high current injector for tandem accelarators . . . B21 (1987) 334
Ogawa, K., see Ishikawa, J. . . . B21 (1987) 205
Ohira, S. and M. Iwaki, Aluminum surface modification by a non-mass-analyzed nitrogen ion beam . . . B21 (1987) 588
Okamoto, K., see Yabe, E. . . . B21 (1987) 190
Okamoto, K., see Tonegawa, A. . . . B21 (1987) 212
Opsal, J., see Smith, W.L. . . . B21 (1987) 537
Opsal, J., see Schuur, J. . . . B21 (1987) 554
Outcault, R., C. McKenna, T. Robertson and L. Biondo, A new computer designed Faraday system for high current ion implantation systems . . . B21 (1987) 354
Ozarski, R.G., see Golin, J.R. . . . B21 (1987) 542

Pal, P.B., V.P. Varshney and D.K. Gupta, Approximate expressions for continuous slowing down approximation ranges of high energy electrons and positrons . . . B21 (1987) 14
Parilis, E.S., see Bitensky, I.S. . . . B21 (1987) 26
Parisi, N., see Aitken, D. . . . B21 (1987) 622
Park, H.-S., see Price, P.B. . . . B21 (1987) 60
Partyka, J., see Mączka, D. . . . B21 (1987) 521
Paulson, W.M., see Wilson, S.R. . . . B21 (1987) 433
Pavlyak, F., see Krafcsik, I. . . . B21 (1987) 604
Pleshkov, G.A., see Adishchev, Yu.N. . . . B21 (1987) 49
Plumb, F.G., see Steen, L.S. . . . B21 (1987) 328
Posselt, M. and W. Skorupa, The electronic stopping and range profile calculations for high energy implantation of phosphorous into silicon . . . B21 (1987) 8
Potylitsin, A.P., see Adishchev, Yu.N. . . . B21 (1987) 49
Powell, R.A., see Felch, S.B. . . . B21 (1987) 486
Pramanik, D. and A.N. Saxena, Programming of ROMs after metal definition using MeV ion implantation . . . B21 (1987) 116
Pramanik, D. and A.N. Saxena, Measurement of temperature profiles across single wafers in rapid thermal annealers . . . B21 (1987) 618
Pranevičius, L., see Galkute, L. . . . B21 (1987) 46
Pranevičius, L., see Domkus, M. . . . B21 (1987) 480
Pranevičius, L., see Augulis, L. . . . B21 (1987) 608
Price, P.B., H.-S. Park, G. Gerbier, J. Drach and M.H. Salamon, VG-13: a nuclear-track-recording glass detector with uniquely high resolution . . . B21 (1987) 60
Proudfoot, G., T.S. Green, M. Inman and C.M.O. Mahony, Development of a 200 kV high current accelerator with post acceleration mass analysis for O^+ implantation into silicon . . . B21 (1987) 300
Pruitt, C., see Steen, L.S. . . . B21 (1987) 328
Prussin, S. and K.S. Jones, The effect of implant species on defect anneal kinetics part I: silicon and phosphorus implantation . . . B21 (1987) 496
Prussin, S., see Jones, K.S. . . . B21 (1987) 499
Puodžiukynas, L., see Domkus, M. . . . B21 (1987) 480
Purser, K.H., see Turner, N. . . . B21 (1987) 285

Rai, A.K., J.A. Baker, D.C. Ingram, A.W. McCormick and D.A. Walsh, Damage profiles of MeV implants of Ga and Si in silicon . . . B21 (1987) 466
Rangelow, I.W., see Kakoschke, R. . . . B21 (1987) 142
Raparia, D., see DiBitonto, D. . . . B21 (1987) 155

Rathmell, R.D. and G.A. Norton, Production MeV ion implanters for energies from 200 keV to 4 MeV B21 (1987) 270
Rausch, W., see Gelpey, J.C. B21 (1987) 612
Reeson, K.J., see Hemment, P.L.F. B21 (1987) 129
Riedl, P., see Krafcsik, I. B21 (1987) 604
Riemenschneider, P., see Tejwani, M.J. B21 (1987) 471
Rigik, M., see Smith, A.K. B21 (1987) 529
Robertson, T., see Outcault, R. B21 (1987) 354
Robinson, L., see Steen, L.S. B21 (1987) 328
Röhl, S., see Kakoschke, R. B21 (1987) 142
Rosencwaig, A., see Smith, W.L. B21 (1987) 537
Rosencwaig, A., see Schuur, J. B21 (1987) 554
Ruffell, J.P., D.H. Douglas-Hamilton, R.E. Kaim and K. Izumi, A high current, high voltage oxygen ion implanter B21 (1987) 229
Ruffell, J.P., see Kaim, R.E. B21 (1987) 321
Ruffell, J.P., see Douglas-Hamilton, D.H. B21 (1987) 324
Russo, C.J., see Aitken, D. B21 (1987) 622
Russo, C.J., see Mehta, S. B21 (1987) 629

Saito, T., H. Yamakawa, S. Komiya, H.J. Kang and R. Shimizu, Dynamic simulation of ion implantation with damaging processes included B21 (1987) 456
Sakudo, N., Microwave ion source for ion implantation B21 (1987) 168
Salamon, M.H., see Price, P.B. B21 (1987) 60
Saler, S., see Kakoschke, R. B21 (1987) 142
Sampayan, S.E., see King, M.L. B21 (1987) 396
Sanfacon, M., see Bunker, S.N. B21 (1987) 148
Saxena, A.N., see Pramanik, D. B21 (1987) 116
Saxena, A.N., see Pramanik, D. B21 (1987) 618
Scaife, W., The Veeco 4840 automated implant system B21 (1987) 258
Schell, N.W., see Golin, J.R. B21 (1987) 542
Schuur, J., C. Waters, J. Maneval, N. Tripsis, A. Rosencwaig, M. Taylor, W.L. Smith, L. Golding and J. Opsal, Relaxation of ion implant damage in silicon wafers at room temperature measured by thermal waves and double implant sheet resistance B21 (1987) 554
Schwartz, V., see Aitken, D. B21 (1987) 622
Seerveld, J.L., see Wilson, S.R. B21 (1987) 433
Seidel, T.E., CMOS process review with implications for ion implantation B21 (1987) 96
Sethuramiah, A., see Shrivastava, S. B21 (1987) 591
Setvak, M., Some problems in particulate acceleration B21 (1987) 378
Shi Zhi Zu, see Jiang Xin Yuan B21 (1987) 310
Shibuya, T., see Yabe, E. B21 (1987) 190
Shimada, M., see Torii, Y. B21 (1987) 178
Shimizu, R., see Saito, T. B21 (1987) 456
Shimoyama, T., see Tonegawa, A. B21 (1987) 212
Shrivastava, S., A. Jain, A. Sethuramiah, V.D. Vankar and K.L. Chopra, Wear behaviour of nitrogen implanted stainless steel B21 (1987) 591
Sieradzki, M., see Turner, N. B21 (1987) 285
Sigmon, T.W., see Kao, T.-M. B21 (1987) 578
Simcox, G., see Glavish, H.F. B21 (1987) 264
Simonis, H.J., F. Hagelberg, W. Trölenberg, K.-H. Speidel, M. Knopp and J. Gerber, The effect of helium layers implanted into thin iron foils on transient magnetic fields B21 (1987) 56
Simonton, R., see Milgate, R. B21 (1987) 381
Simonton, R.B., The use of self-implanted amorphized silicon substrates to eliminate channeling effects in low energy boron implants B21 (1987) 490
Singh, G., see Virk, H.S. B21 (1987) 68
Sioshansi, P., see Bunker, S.N. B21 (1987) 148
Sioshansi, P., see Bricault, R.J. B21 (1987) 586
Siu, B., see Tzeng, J.C. B21 (1987) 112
Skorupa, W., see Posselt, M. B21 (1987) 8
Smith, A.K., W.H. Johnson, W.A. Keenan, M. Rigik and R. Kleppinger, Sheet resistance monitoring of low dose implants using the double implant technique B21 (1987) 529
Smith, G.A., see Bunker, S.N. B21 (1987) 148

Smith, H.E., G.H. Morrison and D.T. Hodul, Crystalline state information from secondary ion mass spectrometry . . . B21 (1987) 503
Smith, S., see Eddy, R. . . . B21 (1987) 424
Smith, T.C., Status of IC applications of ion implantation . . . B21 (1987) 90
Smith, W.L., A. Rosencwaig, D.L. Willenborg, J. Opsal and M.W. Taylor, Ion implant monitoring with thermal wave technology . . . B21 (1987) 537
Smith, W.L., see Schuur, J. . . . B21 (1987) 554
Smith, W.L., see Wendman, M.A. . . . B21 (1987) 559
Soni, A., see Higashi, H. . . . B21 (1987) 518
Southwood, P.D. and N.J. Bright, Integrated factory interface for the precision implant 9000 ion implanter operator. Operator, service personnel, factory management host, and remote diagnostics . . . B21 (1987) 514
Speidel, K.-H., see Simonis, H.J. . . . B21 (1987) 56
Spinelli, P., A.M. Cartier and M. Bruel, Critical aspects of high energy implants for CMOS technology: channeling effects and masking problems . . . B21 (1987) 452
Spinelli, P., see Biasse, B. . . . B21 (1987) 493
Splinter, P., see Taylor, C. . . . B21 (1987) 224
Steen, L.S., J.M. Hall, D. Aitken, F.G. Plumb, M.T. Wauk, N. Bright, C. Pruitt and L. Robinson, The precision implant 9000, a new concept in ion implantation systems . . . B21 (1987) 328
Strathman, E., see Ingram, D.C. . . . B21 (1987) 460
Strathman, E.M., see Wong, H. . . . B21 (1987) 447
Strathman, M.D., see Wong, H. . . . B21 (1987) 447
Stultz, T., see Kermani, A. . . . B21 (1987) 633
Stump, P.O., see Gelpey, J.C. . . . B21 (1987) 612
Suzuki, T., see Uchiyama, T. . . . B21 (1987) 306
Swenson, C., see DiBitonto, D. . . . B21 (1987) 155

Takagi, K., see Yabe, E. . . . B21 (1987) 190
Takagi, K., see Tonegawa, A. . . . B21 (1987) 212
Takagi, K., see Komatsu, K. . . . B21 (1987) 235
Takagi, K., see Uchiyama, T. . . . B21 (1987) 306
Takagi, T., see Yamada, I. . . . B21 (1987) 120
Takagi, T., see Ishikawa, J. . . . B21 (1987) 186
Takagi, T., see Ishikawa, J. . . . B21 (1987) 205
Takayama, K., see Yabe, E. . . . B21 (1987) 190
Takayama, K., see Takeshiro, S. . . . B21 (1987) 209
Takayama, K., see Tonegawa, A. . . . B21 (1987) 212
Takeda, M., see Wada, T. . . . B21 (1987) 574
Takeshiro, S., K. Takayama, T. Hatori and T. Watanabe, Numerical simulation for the discharge mechanism of a TP-D plasma source . . . B21 (1987) 209
Tamura, M., N. Natsukai, Y. Wada and E. Mitani, MeV-energy B^+, P^+ and As^+ ion implantation into Si . . . B21 (1987) 438
Taylor, C., P. Splinter, A. Weed, J. Grant and S. Holden, 200 mm end station for ion beam implanters . . . B21 (1987) 224
Taylor, M., see Schuur, J. . . . B21 (1987) 554
Taylor, M.W., see Smith, W.L. . . . B21 (1987) 537
Tejwani, M.J. and P. Riemenschneider, Monte Carlo simulation of recoil range distributions in multilayer GaAs targets . . . B21 (1987) 471
Terasawa, T., see Komatsu, K. . . . B21 (1987) 317
Thayer III, R.B., XP series high current ion implantation systems for up to 200 mm wafer processing . . . B21 (1987) 245
Thompson, T., see Wonson, C. . . . B21 (1987) 523
Tian Wei, Li Jiun, Cao Niansen and Cai Weiping, Effect of the target temperature on the surface modification of Cr-deposited Fe by ion beam mixing . . . B21 (1987) 597
Ting, C., see Tzeng, J.C. . . . B21 (1987) 112
Tkach, J., see Eddy, R. . . . B21 (1987) 424
Tohi, A., see Yoshida, M. . . . B21 (1987) 483
Tomchakov, V.K., see Adishchev, Yu.N. . . . B21 (1987) 49
Tonegawa, A., see Yabe, E. . . . B21 (1987) 190
Tonegawa, A., T. Shimoyama, E. Yabe, K. Takayama, K. Takagi, R. Fukui, R. Kikuchi, K. Okamoto and S. Komiya, Plasma compression type hollow cathode ion source . . . B21 (1987) 212
Torii, Y., M. Shimada and I. Watanabe, Very high current ECR ion source for an oxygen ion implanter . . . B21 (1987) 178
Tripsis, N., see Schuur, J. . . . B21 (1987) 554
Trölenberg, W., see Simonis, H.J. . . . B21 (1987) 56
Tsou Shih-chang, see Liu Xiang-huai . . . B21 (1987) 595

Tsou Shih-chang, see Lin Cheng-lu B21 (1987) 627
Tsuji, H., see Ishikawa, J. B21 (1987) 186
Tsuji, H., see Ishikawa, J. B21 (1987) 205
Tsukakoshi, O., see Katagawa, T. B21 (1987) 194
Tsukakoshi, O., see Komatsu, K. B21 (1987) 235
Tsukakoshi, O., see Uchiyama, T. B21 (1987) 306
Tu Yu-shen, see Liu Xiang-huai B21 (1987) 595
Turner, J., see Jost, J. B21 (1987) 372
Turner, N., K.H. Purser and M. Sieradzki, Design considerations of a VLSI compatible production MeV ion implantation system B21 (1987) 285
Tzeng, J.C., W. Baerg, C. Ting and B. Siu, A novel self-aligned oxygen (SALOX) implanted SOI MOSFET device structure B21 (1987) 112

Uchiyama, T., K. Takagi, T. Katagawa, Y. Mihara, R. Fukui, O. Tsukakoshi, R. Kikuchi, A. Isoya, S. Komiya, T. Koshikawa and T. Suzuki, A 400 keV ion accelerator for surface study B21 (1987) 306
Uglov, S.R., see Adishchev, Yu.N. B21 (1987) 49
Urbanus, W.H., see Koudijs, R. B21 (1987) 296

Vankar, V.D., see Shrivastava, S. B21 (1987) 591
Varshney, V.P., see Pal, P.B. B21 (1987) 14
Virk, H.S., S.K. Modgil and G. Singh, Fission track annealing models and the concept of a single activation energy B21 (1987) 68
Vorobiev, S.A., see Adishchev, Yu.N. B21 (1987) 49

Wada, T. and M. Takeda, Electron beam doping in substrates of overlayer Si/substrate GaAs, Si/GaAsP and evaporated Ge/Si B21 (1987) 574
Wada, Y., see Tamura, M. B21 (1987) 438
Walsh, D.A., see Ingram, D.C. B21 (1987) 460
Walsh, D.A., see Rai, A.K. B21 (1987) 466
Walther, S.R., K.N. Leung, K.W. Ehlers and W.B. Kunkel, Generation of oxygen, carbon and metallic ion beams by a compact microwave source B21 (1987) 215
Wang Xiuqing, see Zheng Lirong B21 (1987) 601
Washburn, J., see Brown, I. B21 (1987) 201
Watanabe, I., see Torii, Y. B21 (1987) 178
Watanabe, T., see Takeshiro, S. B21 (1987) 209
Waters, C., see Schuur, J. B21 (1987) 554
Wauk, M.T., New ion implantation system with advanced process capabilities B21 (1987) 280
Wauk, M.T., see Steen, L.S. B21 (1987) 328
Weber, E.R., see Jones, K.S. B21 (1987) 499
Weed, A., see Taylor, C. B21 (1987) 224
Week, K., see Higashi, H. B21 (1987) 518
Wei Zongying, see Feng Xiqi B21 (1987) 576
Weiss, B.L. and J.M. Naden, The effect of sample temperature on the structure of He^+ implanted optical waveguides in $LiNbO_3$ B21 (1987) 584
Wendman, M.A. and W.L. Smith, Thermal wave implant dosimetry for process control on product wafers B21 (1987) 559
White, N.R., Computers and the design of ion beam optical systems B21 (1987) 339
Willenborg, D.L., see Smith, W.L. B21 (1987) 537
Wilson, C.G., see Giles, I.S. B21 (1987) 72
Wilson, S.R., W.M. Paulson, R.B. Gregory, B.C. Lamartine, J.A. Leavitt, L.C. McIntyre Jr and J.L. Seerveld, Amorphization implants and low temperature rapid thermal processing to form low sheet resistance, shallow junction, boron implanted layers B21 (1987) 433
Winterbon, K.B., Finite-angle multiple scattering B21 (1987) 1
Wolf, G.K., K. Zucholl, M. Barth and W. Ensinger, Equipment for ion beam assisted deposition B21 (1987) 570
Wong, H., see Deng, E. B21 (1987) 134
Wong, H., E. Deng, N.W. Cheung, P.K. Chu, E.M. Strathman and M.D. Strathman, Profile studies of MeV ions implanted into Si B21 (1987) 447
Wonson, C. and T. Thompson, Intelligent performance optimization for a fully automatic high current ion implantation system B21 (1987) 523

Yabe, E., N. Ishizaka, T. Shibuya, A. Tonegawa, K. Takayama, R. Fukui, K. Takagi, R. Kikuchi, K. Okamoto and S. Komiya, Plasma filament ion source for high current implanter B21 (1987) 190

Yabe, E., see Tonegawa, A. B21 (1987) 212
Yamada, I. and T. Takagi, Current status of ionized-cluster beam technique: a low energy ion beam deposition B21 (1987) 120
Yamakawa, H., see Saito, T. B21 (1987) 456
Yano, T., see Yuba, Y. B21 (1987) 151
Yoshida, M., A. Tohi and M. Inoue, Deep p-type layer formation using Al^+ implantation and diffusion into Si B21 (1987) 483
Yuba, Y., T. Yano, T. Ishida, K. Gamo and S. Namba, Deep levels induced by focused ion implantation in GaAs B21 (1987) 151
Yui, K., see Komatsu, K. B21 (1987) 317

Zanini, V., see Margesin, B. B21 (1987) 566
Zappe, H.P. and C. Hu, Device characteristics of MOSFETs in MeV implanted substrates B21 (1987) 163
Zhang, J.-P., see Cui, F.-Z. B21 (1987) 478
Zhao Chuanguo, see Jin Jiucheng B21 (1987) 610
Zheng Lirong and Wang Xiuqing, The preparation of i-c films with low ion beams B21 (1987) 601
Zhou Fengsheng, see Ma Mingxiu B21 (1987) 182
Zimmermann, L., see Garvey, E. B21 (1987) 509
Zou Weiyuan, see Feng Xiqi B21 (1987) 576
Zrudsky, D.R., see Myron, D.D. B21 (1987) 410
Zubauskas, G., see Galkute, L. B21 (1987) 46
Zubauskas, G., see Domkus, M. B21 (1987) 480
Zucholl, K., see Wolf, G.K. B21 (1987) 570

Nuclear Instruments and Methods in Physics Research B21 (1987) 649–653
North-Holland, Amsterdam

SUBJECT INDEX

Basic data for materials modification and analysis

Finite-angle multiple scattering, Winterbon, K.B. B21 (1987) 1
The electronic stopping and range profile calculations for high energy implantation of phosphorous into silicon, Posselt, M. and W. Skorupa B21 (1987) 8
Approximate expressions for continuous slowing down approximation ranges of high energy electrons and positrons, Pal, P.B., V.P. Varshney and D.K. Gupta B21 (1987) 14
The scattering of doubly charged ions from surfaces, Chapman, G.E., D.J. O'Connor and R.J. MacDonald B21 (1987) 20

Atomic collisions in solids

Shock wave mechanism for cluster emission and organic molecule desorption under heavy ion bombardment, Bitensky, I.S. and E.S. Parilis B21 (1987) 26
Analytical expressions for the internal and kinetic energy distributions of sputtered clusters and molecules, Hoogerbrugge, R. and P.G. Kistemaker B21 (1987) 37
Model of preferential sputtering of multicomponent materials induced by low energy ions, Galkute, L., L. Pranevičius and G. Zubauskas B21 (1987) 46
Measurements of parametric X-rays from relativistic electrons in silicon crystals, Adishchev, Yu.N., A.N. Didenko, V.V. Mun, G.A. Pleshkov, A.P. Potylitsin, V.K. Tomchakov, S.R. Uglov and S.A. Vorobiev B21 (1987) 49

Ion beam modification of materials

The effect of helium layers implanted into thin iron foils on transient magnetic fields, Simonis, H.J., F. Hagelberg, W. Trölenberg, K.-H. Speidel, M. Knopp and J. Gerber B21 (1987) 56

Effects of radiation

VG-13: a nuclear-track-recording glass detector with uniquely high resolution, Price, P.B., H.-S. Park, G. Gerbier, J. Drach and M.H. Salamon B21 (1987) 60
Fission track annealing models and the concept of a single activation energy, Virk, H.S., S.K. Modgil and G. Singh B21 (1987) 68

Analysis of materials

A simple bevelling technique for the depth-profiling of deuterium in steels, Giles, I.S. and C.G. Wilson B21 (1987) 72
Absolute determination of 10^{12} cm^{-2} As in Si by RBS microanalysis (*Letter to the Editor*), Abel, F., B. Agius and J. Gyulai B21 (1987) 77

Experimental methods and equipment

Proceedings of the Sixth International Conference on Ion Implantation Technology (Berkeley, CA, USA, July 28–August 1, 1986)

Section I. Reviews

Historical perspectives on ion implantation, Gibbons, J.F. B21 (1987) 83
Status of IC applications of ion implantation, Smith, T.C. B21 (1987) 90
CMOS process review with implications for ion implantation, Seidel, T.E. B21 (1987) 96

0168-583X/87/$03.50 © Elsevier Science Publishers B.V.
(North-Holland Physics Publishing Division)

Section II. Challenges and emerging technologies

Maskless ion implantation system for three-dimensional fine doping structures in III–V compound semiconductors, Miyauchi, E. and H. Hashimoto B21 (1987) 104
A novel self-aligned oxygen (SALOX) implanted SOI MOSFET device structure, Tzeng, J.C., W. Baerg, C. Ting and B. Siu B21 (1987) 112
Programming of ROMs after metal definition using MeV ion implantation, Pramanik, D. and A.N. Saxena B21 (1987) 116
Current status of ionized-cluster beam technique: a low energy ion beam deposition, Yamada, I. and T. Takagi . B21 (1987) 120
Applications of SIMOX technology to CMOS LSI and radiation-hardened devices, Izumi, K. B21 (1987) 124
Novel dielectric/silicon planar structures formed by ion beam synthesis, Hemment, P.L.F., K.J. Reeson, J.A. Kilner, R.J. Chater, C. Marsh, G.R. Booker, J.R. Davis and G.K. Celler B21 (1987) 129
Effects of high energy boron ions implanted in MOSFETs, Deng, E., H. Wong and N.W. Cheung B21 (1987) 134
Ion implantation into three-dimensional structures, Kakoschke, R., H. Binder, S. Röhl, K. Masseli, I.W. Rangelow, S. Saler and R. Kassing B21 (1987) 142
Analysis of buried layers from high dose oxygen ion implantation, Bunker, S.N., P. Sioshansi, M. Sanfacon, A. Mogro-Campero and G.A. Smith B21 (1987) 148
Deep levels induced by focused ion implantation in GaAs, Yuba, Y., T. Yano, T. Ishida, K. Gamo and S. Namba B21 (1987) 151
Multi-MeV ion implantation accelerator system, DiBitonto, D., R. Huson, P. McIntyre, A. Nassiri, D. Raparia and C. Swenson B21 (1987) 155
Layer thicknesses in oxygen implantation of silicon, Douglas-Hamilton, D.H., R.P. Dolan and H.E. Friedman . B21 (1987) 158
Device characteristics of MOSFETs in MeV implanted substrates, Zappe, H.P. and C. Hu B21 (1987) 163

Section III. Sourcery

Microwave ion source for ion implantation, Sakudo, N. B21 (1987) 168
Very high current ECR ion source for an oxygen ion implanter, Torii, Y., M. Shimada and I. Watanabe B21 (1987) 178
A hollow cold cathode multipurpose ion source, Ma Mingxiu, Li Junping and Zhou Fengsheng B21 (1987) 182
Impregnated-electrode-type liquid metal ion source, Ishikawa, J., Y. Gotoh, H. Tsuji and T. Takagi B21 (1987) 186
Plasma filament ion source for high current implanter, Yabe, E., N. Ishizaka, T. Shibuya, A. Tonegawa, K. Takayama, R. Fukui, K. Takagi, R. Kikuchi, K. Okamoto and S. Komiya B21 (1987) 190
Application of a 3-D computer simulation code for ion beam extraction with a high current Freeman type ion source, Katagawa, T., O. Tsukakoshi, S. Komiya and N. Inoue B21 (1987) 194
Basics of ion sources in BASIC (BIOSIB), Ghanbari, E. B21 (1987) 198
The MEVVA ion source for high current metal ion implantation, Brown, I. and J. Washburn B21 (1987) 201
Negative ion source (NIABNIS) and preparation of transparent carbon films by negative carbon ion beam deposition, Ishikawa, J., K. Ogawa, K. Miyata, H. Tsuji and T. Takagi B21 (1987) 205
Numerical simulation for the discharge mechanism of a TP-D plasma source, Takeshiro, S., K. Takayama, T. Hatori and T. Watanabe B21 (1987) 209
Plasma compression type hollow cathode ion source, Tonegawa, A., T. Shimoyama, E. Yabe, K. Takayama, K. Takagi, R. Fukui, R. Kikuchi, K. Okamoto and S. Komiya B21 (1987) 212
Generation of oxygen, carbon and metallic ion beams by a compact microwave source, Walther, S.R., K.N. Leung, K.W. Ehlers and W.B. Kunkel B21 (1987) 215

Section IV. New equipment and systems

Radio-frequency linear accelerators for ion implanters, Glavish, H.F. B21 (1987) 218
200 mm end station for ion beam implanters, Taylor, C., P. Splinter, A. Weed, J. Grant and S. Holden B21 (1987) 224
A high current, high voltage oxygen ion implanter, Ruffell, J.P., D.H. Douglas-Hamilton, R.E. Kaim and K. Izumi B21 (1987) 229
High current ion implanter aimed at clean and dust-free production, Komatsu, K., K. Takagi, O. Tsukakoshi, T. Katagawa, E. Kouno and S. Komiya B21 (1987) 235
PR-80 high current ion implantation machine, Kawai, T., M. Naitoh, M. Nogami, T. Kinoyama, N. Nagai and H. Fujisawa B21 (1987) 239
XP series high current ion implantation systems for up to 200 mm wafer processing, Thayer III, R.B. B21 (1987) 245
A 100 mA class ion implanter for large scale production of buried oxide SOI wafers, Moffatt, S. B21 (1987) 251
The Veeco 4840 automated implant system, Scaife, W. B21 (1987) 258
Production high energy ion implanters using radio frequency acceleration, Glavish, H.F., D. Bernhardt, P. Biosseau, B. Libby, G. Simcox and A.S. Denholm B21 (1987) 264
Production MeV ion implanters for energies from 200 keV to 4 MeV, Rathmell, R.D. and G.A. Norton B21 (1987) 270
The precision implant 9000 beam line, Aitken, D. B21 (1987) 274

New ion implantation system with advanced process capabilities, Wauk, M.T. B21 (1987) 280
Design considerations of a VLSI compatible production MeV ion implantation system, Turner, N., K.H. Purser and M. Sieradzki B21 (1987) 285
A 1 and 2 MV ion implantation facility, Koudijs, R., P. Dubbelman, W.H. Urbanus and J.G. Bannenberg B21 (1987) 296
Development of a 200 kV high current accelerator with post acceleration mass analysis for O^+ implantation into silicon, Proudfoot, G., T.S. Green, M. Inman and C.M.O. Mahony B21 (1987) 300
A 400 keV ion accelerator for surface study, Uchiyama, T., K. Takagi, T. Katagawa, Y. Mihara, R. Fukui, O. Tsukakoshi, R. Kikuchi, A. Isoya, S. Komiya, T. Koshikawa and T. Suzuki B21 (1987) 306
A 600 keV research heavy ion implanter, Yuan, Jiang Xin, Lu Shi Wan and Shi Zhi Zu B21 (1987) 310
Large diameter ion beam implantation system, Matsuda, K., F. Fukumaru, Y. Mizutani, M. Konishi and K. Matsunaga B21 (1987) 314
A high throughput end station of a high current ion implanter, Komatsu, K., K. Yui, T. Terasawa, K. Niikura, E. Kouno and S. Komiya B21 (1987) 317
Accelaration column for a high current oxygen implanter, Kaim, R.E., D.H. Douglas-Hamilton and J.P. Ruffell B21 (1987) 321
End station design and wafer quality control for a high current oxygen implanter, Douglas-Hamilton, D.H., J.P. Ruffell, R.E. Kaim and K. Izumi B21 (1987) 324
The precision implant 9000, a new concept in ion implantation systems, Steen, L.S., J.M. Hall, D. Aitken, F.G. Plumb, M.T. Wauk, N. Bright, C. Pruitt and L. Robinson B21 (1987) 328
A high current injector for tandem accelarators, O'Connor, J.P. and L.F. Joyce B21 (1987) 334
Computers and the design of ion beam optical systems, White, N.R. B21 (1987) 339

Section V. Process and yield effects

Charging studies in applied metarials precision implant 9000 system, Hall, J.M., H. Glawischnig and W. Holtschmidt B21 (1987) 350
A new computer designed Faraday system for high current ion implantation systems, Outcault, R., C. McKenna, T. Robertson and L. Biondo B21 (1987) 354
A study of wafer and device charging during high current ion implantation, Basra, V.K., C.M. McKenna and S.B. Felch B21 (1987) 360
Wafer cooling in a high current ion implanter, Benveniste, V. B21 (1987) 366
0.5 μm particulate performance of a batch process implanter, Jost, J., G. Angelo and J. Turner B21 (1987) 372
Some problems in particulate acceleration, Setvak, M. B21 (1987) 378
Recent improvements in the particle performance of a Varian 350D ion implanter, Milgate, R. and R. Simonton B21 (1987) 381
A generalized mathematical model for wafer cooling with gas, Evans, D.C. B21 (1987) 385
Planar channeling effects in a batch process ion implanter, Liebert, R.B., D.F. Downey and V.K. Basra B21 (1987) 391
A method of surface charge neutralization during ion implantation, King, M.L., S.E. Sampayan and B.H. Hight B21 (1987) 396

Section VI. Dosimetry

Recent improvements in double charged ion beam energy purity for serial process ion implanters, Kalbfus, C.R. and R. Milgate B21 (1987) 400
Discharge of P^{2+} ions in the beamline of medium current implanters, Brack, K., W. Euen and D. Hagmann ... B21 (1987) 405
Implant uniformity improvement using advanced scanning techniques, Myron, D.D. and D.R. Zrudsky B21 (1987) 410
New dosimetry system for a serial process ion implanter, Lundquist, P., C. McKenna, R. Brick and P. Corey ... B21 (1987) 414
Dosing accuracy: a comparison of several experiments, Larson, L.A. and G.L. Kennedy B21 (1987) 421
Improvements in dose uniformity on high current ion implantation systems, Eddy, R., A. Long, S. Smith and J. Tkach B21 (1987) 424
An etch-study of ion implanted SiO_2 films, Marinescu, R. B21 (1987) 428
0.1% ultra-uniformity in electrostatically scanned ion implantation systems, McGuire, E. B21 (1987) 431

Section VII. Range, damage and shallow junctions

Amorphization implants and low temperature rapid thermal processing to form low sheet resistance, shallow junction, boron implanted layers, Wilson, S.R., W.M. Paulson, R.B. Gregory, B.C. Lamartine, J.A. Leavitt, L.C. McIntyre Jr and J.L. Seerveld B21 (1987) 433
MeV-energy B^+, P^+ and As^+ ion implantation into Si, Tamura, M., N. Natsukai, Y. Wada and E. Mitani B21 (1987) 438
Profile studies of MeV ions implanted into Si, Wong, H., E. Deng, N.W. Cheung, P.K. Chu, E.M. Strathman and M.D. Strathman B21 (1987) 447
Critical aspects of high energy implants for CMOS technology: channeling effects and masking problems, Spinelli, P., A.M. Cartier and M. Bruel B21 (1987) 452

Dynamic simulation of ion implantation with damaging processes included, Saito, T., H. Yamakawa, S. Komiya, H.J. Kang and R. Shimizu ... B21 (1987) 456
Range distributions of MeV implants in silicon II. A comparison of SIMS and spreading resistance profiles of B, P and Ga, Ingram, D.C., J.A. Baker, D.A. Walsh and E. Strathman ... B21 (1987) 460
Damage profiles of MeV implants of Ga and Si in silicon, Rai, A.K., J.A. Baker, D.C. Ingram, A.W. McCormick and D.A. Wâlsh ... B21 (1987) 466
Monte Carlo simulation of recoil range distributions in multilayer GaAs targets, Tejwani, M.J. and P. Riemenschneider ... B21 (1987) 471
Determination of the implanted dopants distribution by Pearson's function, Martan, J. ... B21 (1987) 476
Computer simulations of the ion implantation process in layered materials, Cui, F.-Z., H.-D. Li and J.-P. Zhang B21 (1987) 478
Study of mechanical strains in implanted silicon slices, Domkus, M., L. Augulis, L. Pranevičius, L. Puodžiukynas and G. Zubauskas ... B21 (1987) 480
Deep p-type layer formation using Al^+ implantation and diffusion into Si, Yoshida, M., A. Tohi and M. Inoue . B21 (1987) 483
Use of ultra-low-energy BF_2^+ implantation and rapid annealing to avoid channeling effects in shallow junction formation, Felch, S.B. and R.A. Powell ... B21 (1987) 486
The use of self-implanted amorphized silicon substrates to eliminate channeling effects in low energy boron implants, Simonton, R.B. ... B21 (1987) 490
Formation of shallow P^+N junctions by dual F^+/B^+ implantation, Biasse, B., A.M. Cartier, P. Spinelli and M. Bruel ... B21 (1987) 493
The effect of implant species on defect anneal kinetics part I: silicon and phosphorus implantation, Prussin, S. and K.S. Jones ... B21 (1987) 496
The effect of implant species on defect anneal kinetics part II: arsenic and germanium implantation, Jones, K.S., S. Prussin and E.R. Weber ... B21 (1987) 499
Crystalline state information from secondary ion mass spectrometry, Smith, H.E., G.H. Morrison and D.T. Hodul ... B21 (1987) 503
RTP shallow junction formation of low energy boron implants into preamorphized silicon, Basra, V.K. and D.F. Downey ... B21 (1987) 505

Section VIII. Automation

Robotics and host computer interface for NV-10 high current implanters, Garvey, E. and L. Zimmermann B21 (1987) 509
Integrated factory interface for the precision implant 9000 ion implanter operator. Operator, service personnel, factory management host, and remote diagnostics, Southwood, P.D. and N.J. Bright ... B21 (1987) 514
Process yield improvements with process control terminal for Varian serial ion implanters, Higashi, H., A. Soni, L. Martinez and K. Week ... B21 (1987) 518
Optimization of the ion implantation process, Mączka, D., A. Latuszyński, R. Kuduk and J. Partyka ... B21 (1987) 521
Intelligent performance optimization for a fully automatic high current ion implantation system, Wonson, C. and T. Thompson ... B21 (1987) 523

Section IX. Measurement tools

Monitoring low dose single implanted layers with four-point probe technology, Chen, J.T.C. ... B21 (1987) 526
Sheet resistance monitoring of low dose implants using the double implant technique, Smith, A.K., W.H. Johnson, W.A. Keenan, M. Rigik and R. Kleppinger ... B21 (1987) 529
Ion implant monitoring with thermal wave technology, Smith, W.L., A. Rosencwaig, D.L. Willenborg, J. Opsal and M.W. Taylor ... B21 (1987) 537
Latest advances in ion implant optical dosimetry, Golin, J.R., N.W. Schell, J.A. Glaze and J.G. Ozarski ... B21 (1987) 542
Thermal-wave measurements of ion implanted silicon, Kirby, B.J., L.A. Larson and R.-Y. Liang ... B21 (1987) 550
Relaxation of ion implant damage in silicon wafers at room temperature measured by thermal waves and double implant sheet resistance, Schuur, J., C. Waters, J. Maneval, N. Tripsis, A. Rosencwaig, M. Taylor, W.L. Smith, L. Golding and J. Opsal ... B21 (1987) 554
Thermal wave implant dosimetry for process control on product wafers, Wendman, M.A. and W.L. Smith B21 (1987) 559
Bridging implant technique to characterize MeV implants, Keenan, W.A. ... B21 (1987) 563

Section X. Metals, ceramics, compound semiconductors

An apparatus for combined vapor deposition and ion implantation to modify the surface properties of metals, Margesin, B., F. Giacomozzi, L. Guzman, G. Lazzari and V. Zanini ... B21 (1987) 566
Equipment for ion beam assisted deposition, Wolf, G.K., K. Zucholl, M. Barth and W. Ensinger ... B21 (1987) 570
Electron beam doping in substrates of overlayer Si/substrate GaAs, Si/GaAsP and evaporated Ge/Si, Wada, T. and M. Takeda ... B21 (1987) 574

Ion-beam-induced decomposition of bismuth germanium oxide crystal surfaces, Feng Xiqi, Wei Zongying and Zou Weiyuan B21 (1987) 576
$^{11}B^{+}$ implantation and postimplant anneal studies in $Hg_{1-x}Cd_xTe$, Kao, T.-M. and T.W. Sigmon B21 (1987) 578
Rapid thermal annealing of arsenic, beryllium and zinc dual implanted AlGaAs, Ho, P., Y. Chung and V.W. Aebi B21 (1987) 581
The effect of sample temperature on the structure of He^{+} implanted optical waveguides in $LiNbO_3$, Weiss, B.L. and J.M. Naden B21 (1987) 584
Deposition of boron nitride thin films by ion beam assisted deposition, Bricault, R.J., P. Sioshansi and S.N. Bunker B21 (1987) 586
Aluminum surface modification by a non-mass-analyzed nitrogen ion beam, Ohira, S. and M. Iwaki B21 (1987) 588
Wear behaviour of nitrogen implanted stainless steel, Shrivastava, S., A. Jain, A. Sethuramiah, V.D. Vankar and K.L. Chopra B21 (1987) 591
Improvement of secondary electron emission characteristics by ion implantation, Liu Xiang-huai, Tsou Shih-chang and Tu Yu-shen B21 (1987) 595
Effect of the target temperature on the surface modification of Cr-deposited Fe by ion beam mixing, Tian Wei, Li Jiun, Cao Niansen and Cai Weiping B21 (1987) 597
The preparation of i-c films with low ion beams, Zheng Lirong and Wang Xiuqing B21 (1987) 601
Repetitive mode pulsed ion implanter with magnetically insulated diode, Krafcsik, I., L. Kiralyhidi, P. Riedl, M. Fried, J. Gyulai and F. Pavlyak B21 (1987) 604
Development of surface topology during ion sputtering of silicon, Augulis, L., B. Jasiulionis and L. Pranevičius . B21 (1987) 608
Some experimental studies on GCr15 steel by nitrogen ion overlap-implantation, Jin Jiucheng, Luo Yingming, Zhao Chuanguo and Chen Huanzheng B21 (1987) 610

Section XI. Rapid thermal processing

Uniformity characterization of an RTP system, Gelpey, J.C., P.O. Stump, J. Blake, A. Michel and W. Rausch .. B21 (1987) 612
Measurement of temperature profiles across single wafers in rapid thermal annealers, Pramanik, D. and A.N. Saxena B21 (1987) 618
A new VLSI compatible rapid thermal processing system, Aitken, D., S. Mehta, N. Parisi, C.J. Russo and V. Schwartz B21 (1987) 622
Dopant redistribution of As-implanted SOI films during rapid thermal annealing, Lin Cheng-lu and Tsou Shih-chang B21 (1987) 627
Studies of thin oxides grown by rapid thermal processing, Mehta, S., D.T. Hodul and C.J. Russo B21 (1987) 629
Process control of titanium silicide formation using rapid thermal processing, Kermani, A., T. Debolske, J. Crowley and T. Stultz B21 (1987) 633